

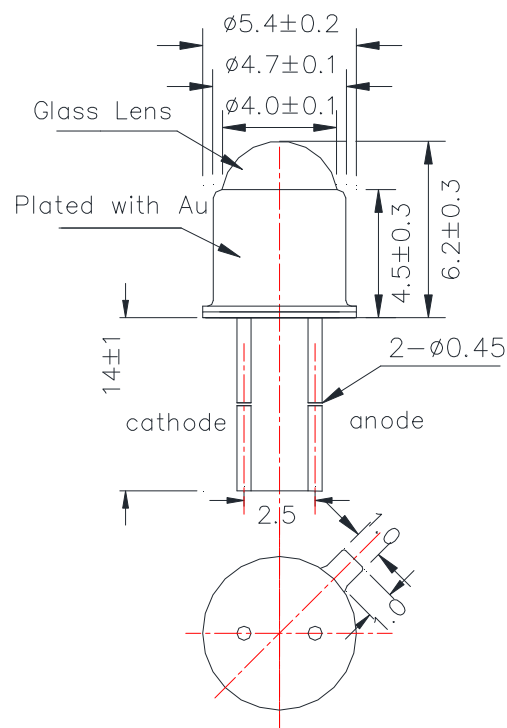
Data Sheet

L570-30M32

Stem type LED Lamp

USHIO

Outline and Internal Circuit



(Unit : mm)

Features

- Non-hermetic package
- Chip Material : AlGaInP
- Chip Dimension : 300um * 300um
- Number of Chips : 1pce
- Peak Wavelength : 570nm typ.
- Stem: TO-18 type
- Lens : Glass Ball Lens
- Cap : Gold Plated

Application

Absolute Maximum Ratings (Tc=25°C)

| Item | Symbol | Ratings | Unit |
|-----------------------|--------|------------|------|
| Power Dissipation | PD | 50 | mW |
| Forward Current | IF | 20 | mA |
| Pulse Forward Current | IFP | 100 | mA |
| Reverse Voltage | VR | 5 | V |
| Thermal Resistance | Rthja | 300 | K/W |
| Junction Temperature | Tj | 120 | °C |
| Operating Temperature | Topr | -40 ~ +100 | °C |
| Storage Temperature | Tstg | -40 ~ +100 | °C |
| Soldering Temperature | TSOL | 250 | °C |

‡Pulse Forward Current condition : Duty 1% and Pulse Width=10us.

‡Soldering condition: Soldering condition must be completed within 5 seconds at 250°C and

is allowed in the area apart 3mm from the bottom of the lamp.

Optical and Electrical Characteristics (Tc=25°C)

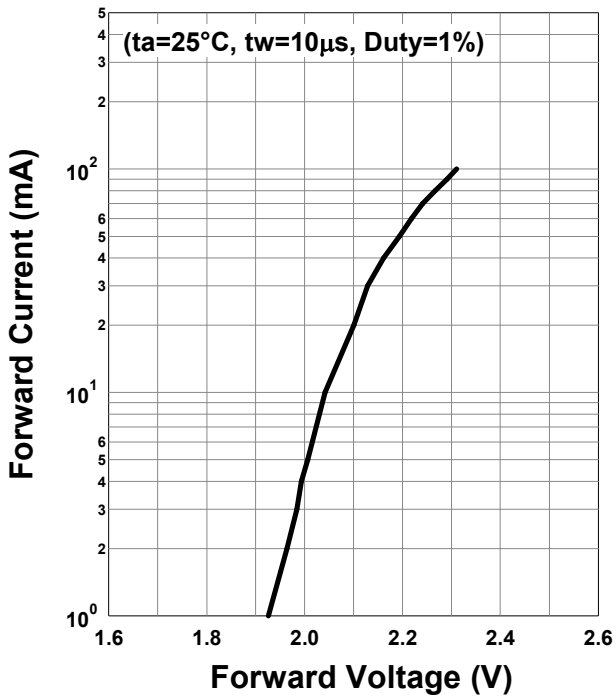
| Parameter | Symbol | Min | Typ | Max | Unit | Test Condition |
|----------------------|--------|-----|------|-----|-------|----------------|
| Forward Voltage | VF | | 2.1 | 2.3 | V | IF=20mA |
| | VFP | | 2.3 | | | IFP=100mA |
| Total Radiated Power | PO | | 0.50 | | mW | IF=20mA |
| | | | 2.7 | | | IFP=100mA |
| Radiant Intensity | IE | | 2.0 | | mW/sr | IF=20mA |
| | | | 10 | | | IFP=100mA |
| Luminous Flux | ΦV | | 330 | | mlm | IF=20mA |
| Peak Wavelength | λp | 560 | | 580 | nm | IF=20mA |
| Dominant Wavelength | λD | | 568 | | nm | IF=20mA |
| Half Width | Δλ | | 11 | | nm | IF=20mA |
| Viewing Half Angle | θ1/2 | | ±13 | | deg. | IF=20mA |
| Rise Time | tr | | 50 | | ns | IF=20mA |
| Fall Time | tf | | 30 | | ns | IF=20mA |

‡ Radiated Power is measured by S3584-08.

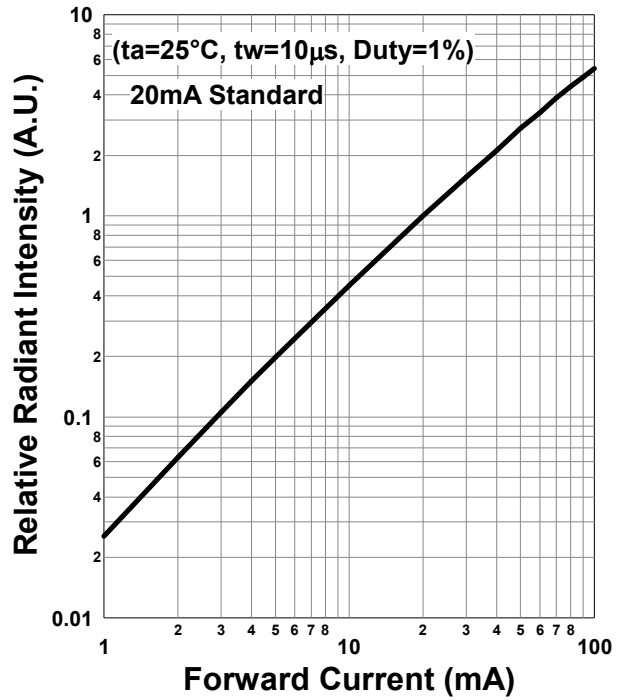
‡ Radiant Intensity is measured by CIE127-2007 Condition B.

Typical Characteristic Curves

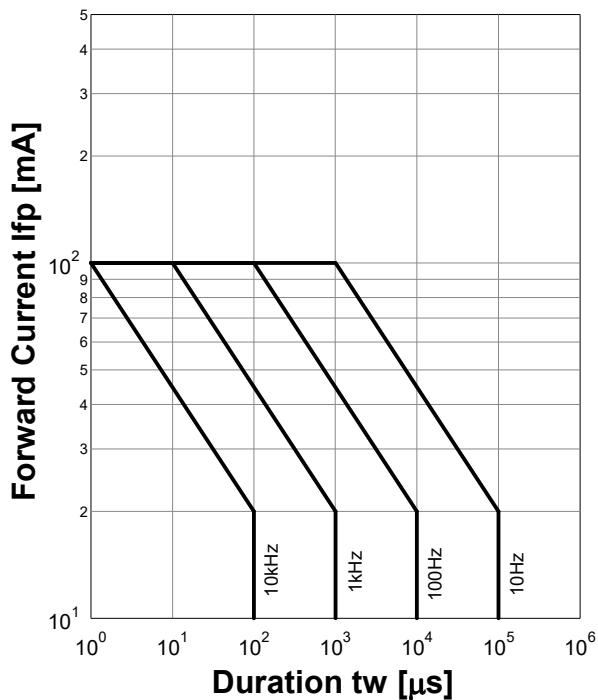
Forward Current - Forward Voltage



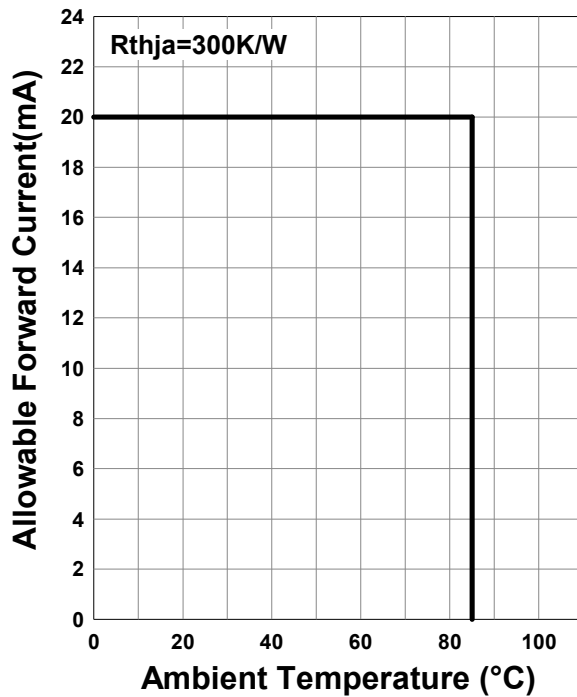
Relative Radiant Intensity - Forward Current



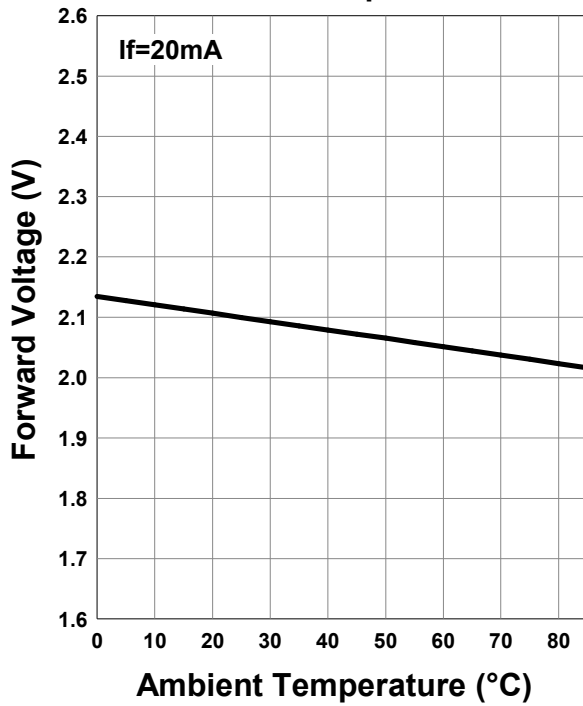
Forward Current - Pulse Duration



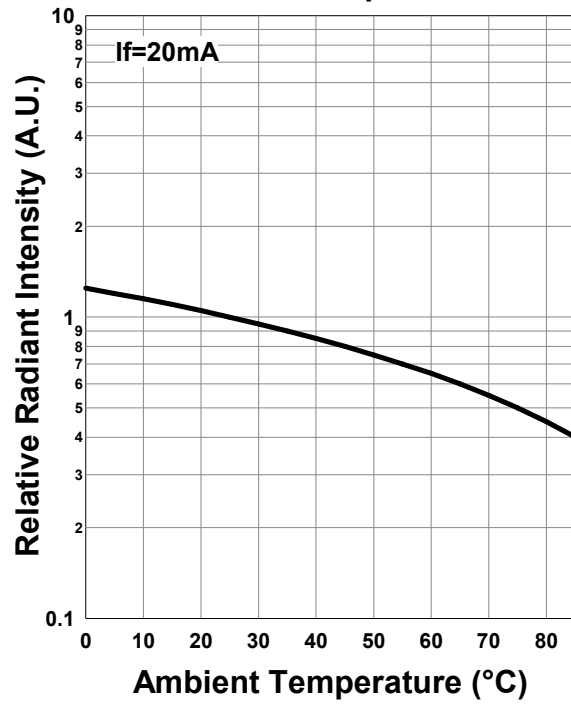
Allowable Forward Current - Ambient Temperature



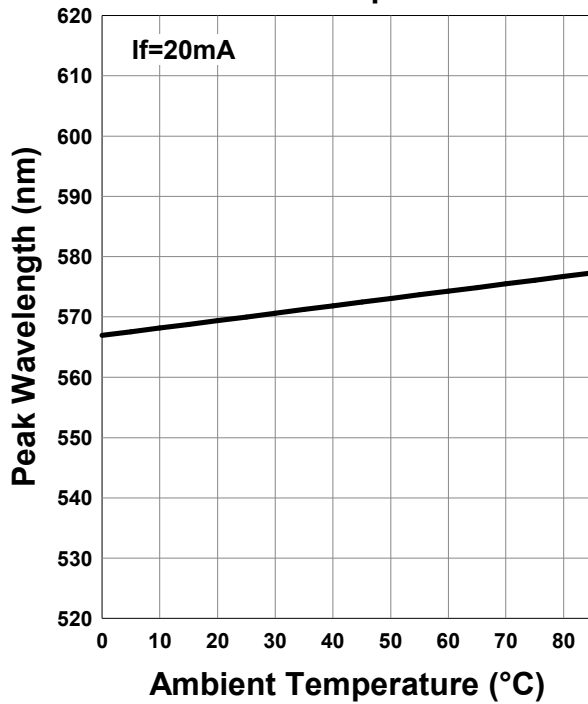
Forward Voltage - Ambient Temperature



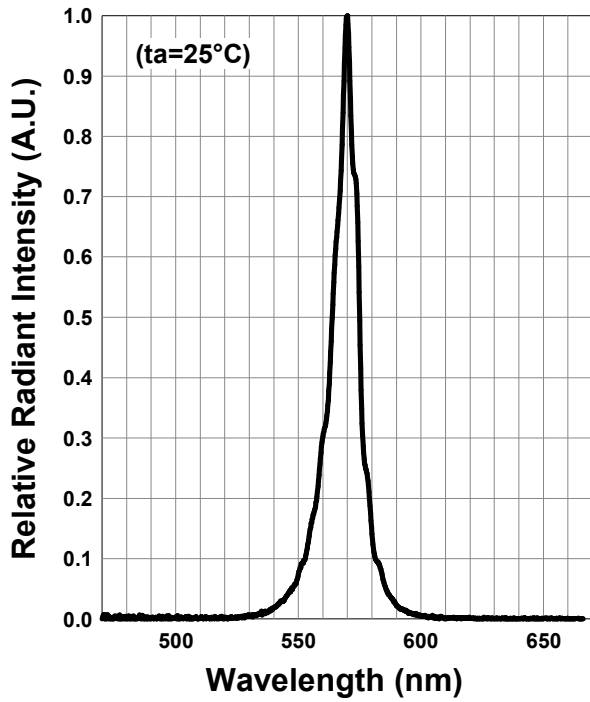
Relative Radiant Intensity - Ambient Temperature



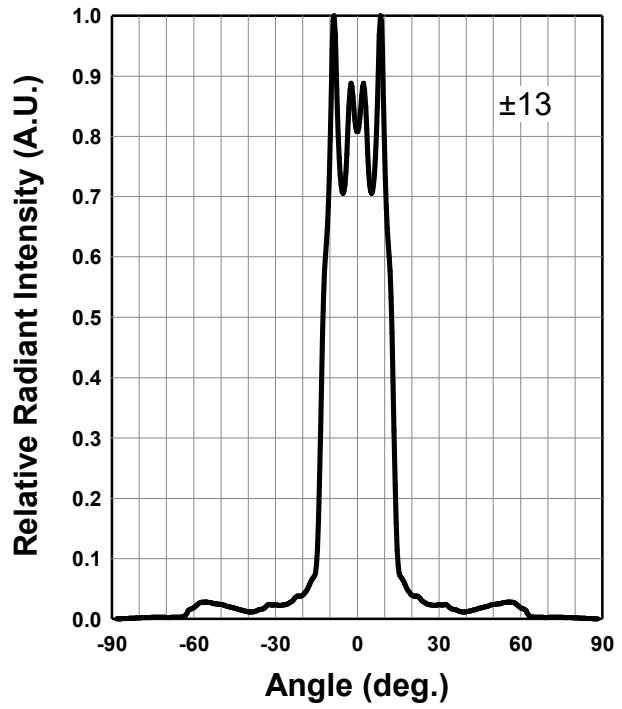
Peak Wavelength - Ambient Temperature



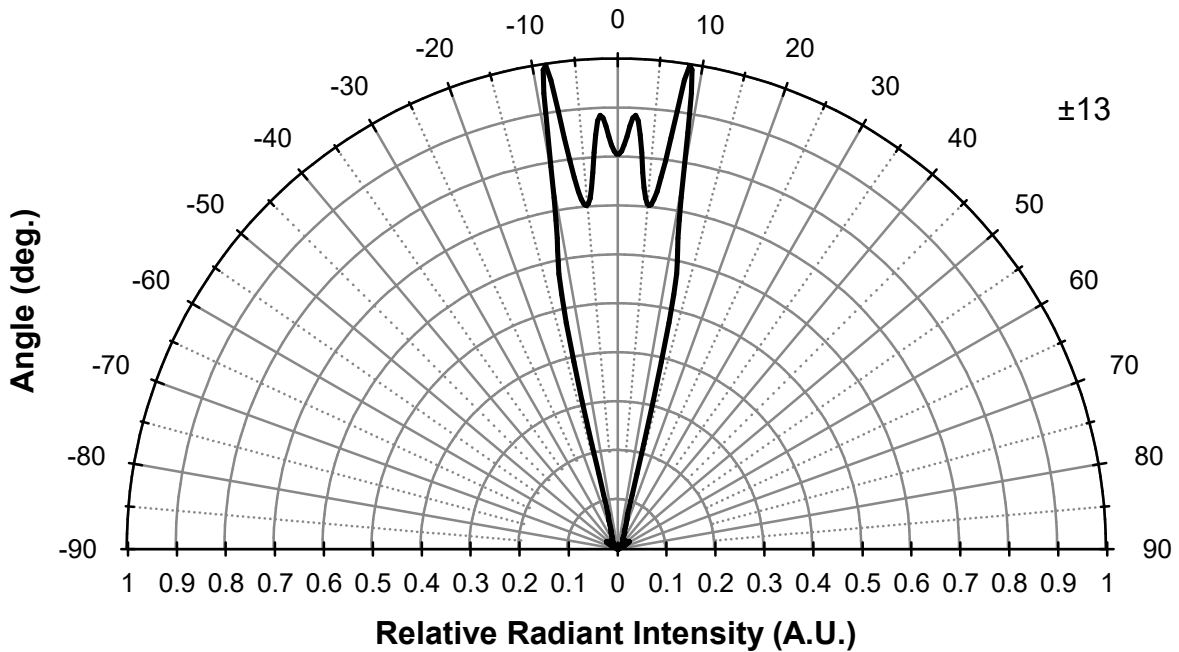
Relative Spectral Emission



Radiation Characteristics



Radiation Characteristics



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Product data and parameters in this catalog are typical values based on reasonably up-to-date measurements.

Product data and parameters may vary by user application and over time.

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